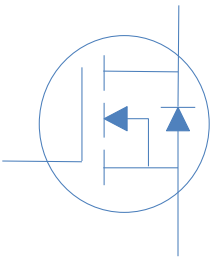
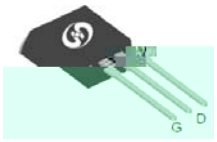
# 150V N-Ch Power MOSFET

| | | | |
|---|---|---|---|
| DS(on),typ | | | |
| | | | |





| Part Number | Package | Marking |
|---|---|---|
| HGW190N15S | | GW190N15S |

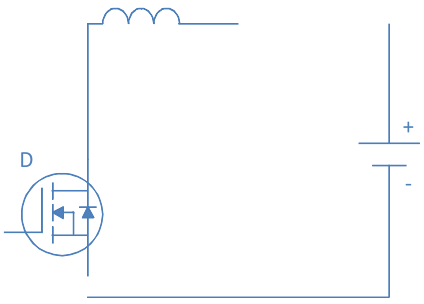
**=25 (unless otherwise specified)**

| Parameter | Symbol | | | |
|---|---|---|---|---|
| Continuous Drain Current | | =25 | | |
| | | =100 | | |
| Drain to Source Voltage | | | | |
| Gate to Source Voltage | | | | |
| Pulsed Drain Current | | | | |
| Avalanche Energy, Single Pulse | E | L=0.3mH, T =25 | | |
| Power Dissipation | P | =25 | | |
| Operating and Storage Temperature | , T | | | |

| Parameter | Symbol | | |
|---|---|---|---|
| Thermal Resistance Junction-Case | | | /W |
| Thermal Resistance Junction-Ambient | | | /W |

| Inductive switching Test | |
|---|---|
| | |

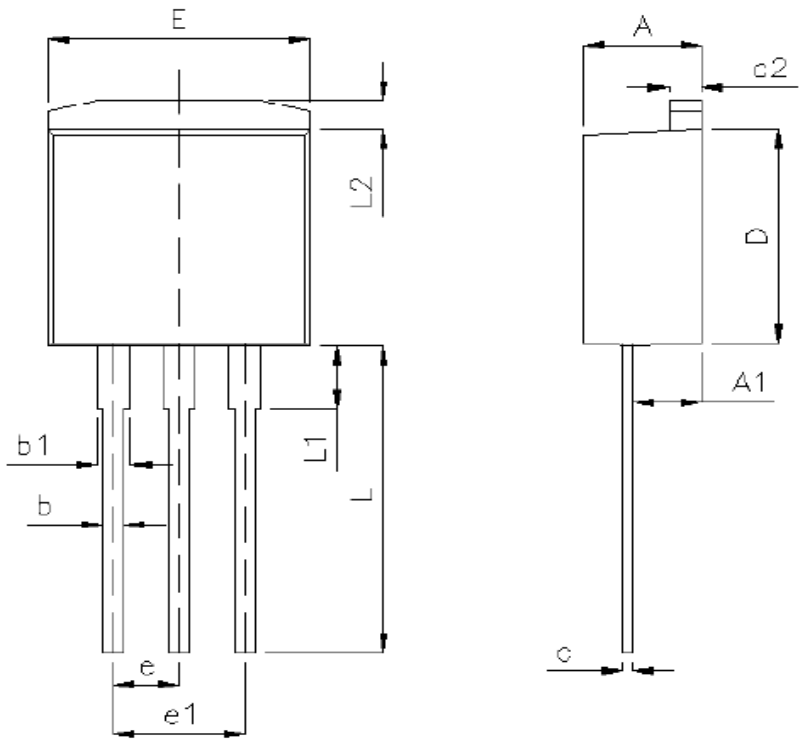
| Gate Charge Test | |
|---|---|
| | |

| Uclamped Inductive Switching (UIS) Test | |
|---|---|
|  | |

| Diode Recovery Test | |
|---|---|
| | |

Package Outline

**TO-262, 3 leads**




UNIT: mm

| | | | | | | | |
|---|---|---|---|---|---|---|---|
| 4.72 | e | 2.44 | 2.54 | 2.64 | A | 4.42 | |
| 2.80 | c1 | 4.98 | | 5.18 | A1 | 2.40 | |
| 0.86 | E | 9.95 | | 10.25 | b | 0.76 | |
| 1.40 | L | 12.50 | | 13.60 | b1 | 1.22 | |
| 0.43 | L1 | 3.30 | 3.50 | 3.80 | c | 0.33 | |
| 1.35 | L2 | 1.22 | | 1.40 | c2 | 1.22 | |
| 9.29 | | | | | D | 8.99 | |